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Product Reliability Information

	Conditions	Duration	Quantity	Rejects
#1 TEST Pre and Post stress electrical test	T_{amb} = 25°C	N/A	All parts	See below
#2 PC Preconditioning	JESD22-A113 Bake T_{amb} = 125°C Soak T_{amb} = 85°C, RH = 85% reflow	24 hours 168 hours 3 cycles	960	0
#5 HTRB High temperature reverse bias	MIL-STD-750-1 T_j = T_j max, V_{DS} = 80% of rated voltage M1039 Method A	1000 hours	2870	0
#6 HTGB High temperature gate bias	JESD22-A108 T_j = T_j max, V_{GS} = 16V	1000 hours	3540	0
#7 TC Temperature Cycling	JESD22-A104 -55°C to 150°C	500 cycles	240	0
#8 UHAST Unbiased highly accelerated stress test	JESD22-A118 T_{amb} = 130°C, RH = 85% Pressure = +2.27atm	96 hours	240	0
#9 HAST Highly accelerated stress test	JESD22-A110 T_{amb} = 130°C, RH = 85% V_{DS} = 80% of rated voltage	96 hours		0
#10 IOL Intermittent operating life	MIL-STD-750 method 1037 ΔTj = 80°C	5000 cycles	240	0
#20 RSH Resistance to solder heat	JESD22-A111 (SMD) 260°C ± 5°C	10s	180	0

#21 SD Solderability	IPC/ECA J-STD-002 Method A dip and look No aging, solder Ta = 245°C	3 sec dip	180	0
	IPC/ECA J-STD-002 Method B dip and look No aging Solder Ta = 245°C >95% lead coverage required Steam Aging: condition C Steam Ta = 93°C, 8 hours Solder Ta = 245°C, 3 sec dip	8 hours 3 sec dip	180	0
	Dry Bake: Ta = 150°C Solder Ta = 245°C >95% lead coverage required	16 hours 3 sec dip	180	0

Calculation of FIT and MTBF

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB) and High temperature Gate Bias (HTGB). Confidence level 60%, derated to 55°C, activation energy 0.7Ev test time 168 to 1000 hours.

Wafer Fab	Technology	Quantity	Failure rate	MTBF
VIS	TrenchMOS	6410	0.19	5.23E+09

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